

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the divisional application:

Listing of Claims:

Claims 1-22 (cancelled):

Claim 23 (original): An implantable cardiac defibrillator circuit comprising:

a low voltage section for providing a control signal;

a high voltage section having an output for powering a load; and

a bridge section capacitively coupling the low voltage section to the high voltage section, the bridge section adapted to operate the high voltage section in response to a signal from the low voltage section.

Claim 24 (original): An implantable cardiac defibrillator circuit according to claim 23 wherein the bridge section further comprises a high portion adapted to operate the high voltage section in response to a high signal from the low voltage section and a low portion adapted to operate the high voltage section in response to a low signal from the low voltage section.

Claim 25 (original): An implantable cardiac defibrillator circuit according to claim 23 wherein the bridge section comprises an integrated circuit.

Claim 26 (original): An implantable cardiac defibrillator circuit according to claim 24 wherein the bridge section high portion and bridge section low portion comprise a first and a second integrated circuit.

Claim 27 (original): An implantable cardiac defibrillator circuit according to claim 23 wherein the bridge section comprises an integrated circuit and an external isolation capacitor.

Claim 28 (original): An implantable cardiac defibrillator circuit according to claim 23 wherein the low voltage section further comprises at least one isolation capacitor.

Claim 29 (original): An implantable cardiac defibrillator circuit according to claim 24 further comprising:

a first transistor having its base and emitter terminals coupled with the high voltage section for supplying power to the load, and its gate operably coupled to the high portion of the bridge section; and

a second transistor having its base and emitter terminals coupled with the high voltage section for supplying power to the load, and its gate operably coupled to the low portion of the bridge section.

Claim 30 (original): An implantable cardiac defibrillator circuit according to claim 29 wherein the bridge section high portion and low portion each further comprise:

an isolation capacitor having one terminal coupled to the low voltage portion output;

a forward-biased diode and first and second reverse-biased diodes coupled to the opposing terminal of the isolation capacitor;

a resistor and capacitor (RC) pair coupled in parallel with the forward-biased diode and the first reverse-biased diode; and

an NMOSFET having its gate terminal coupled with the RC and first reverse-biased diode, and its source terminal coupled with the RC pair, forward-biased diode and gate of the first

transistor, and its drain terminal coupled with the second reverse-biased diode and base of the first transistor.

Claim 31 (original): The implantable cardiac defibrillator circuit of claim 23 adapted for use with a low voltage section output within a frequency range of approximately 1 MHz-10MHz.

Claim 32 (original): The implantable cardiac defibrillator circuit of claim 23 wherein the RC pair is selected to exhibit a time constant within a range of approximately three to ten times longer than the minimum frequency used for the low voltage portion output.

Claim 33 (original): The implantable cardiac defibrillator circuit of claim 23 wherein the diodes comprise N+ substrate P- well bipolar transistors.